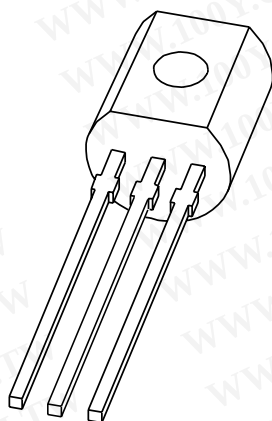


DATA SHEET

勝特力材料 886-3-5753170
勝特力电子(上海) 86-21-54151736
勝特力电子(深圳) 86-755-83298787
[Http://www.100y.com.tw](http://www.100y.com.tw)



BC549; BC550 NPN general purpose transistors

Product specification
Supersedes data of 1997 Jun 20

1999 Apr 22

NPN general purpose transistors

BC549; BC550

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

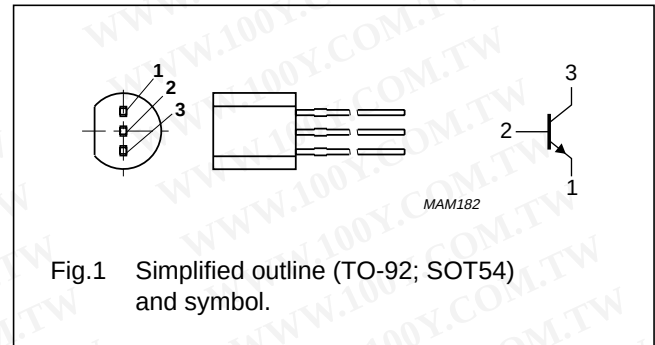
- Low noise stages in audio frequency equipment.

DESCRIPTION

NPN transistor in a TO-92; SOT54 plastic package.
PNP complements: BC559 and BC560.

PINNING

PIN	DESCRIPTION
1	emitter
2	base
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	—	30	V
	BC549		—	50	V
	BC550				
V_{CEO}	collector-emitter voltage	open base	—	30	V
	BC549		—	45	V
	BC550				
V_{EBO}	emitter-base voltage	open collector	—	5	V
I_C	collector current (DC)		—	100	mA
I_{CM}	peak collector current		—	200	mA
I_{BM}	peak base current		—	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25^\circ\text{C}$; note 1	—	500	mW
T_{stg}	storage temperature		-65	+150	$^\circ\text{C}$
T_j	junction temperature		—	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		-65	+150	$^\circ\text{C}$

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	250	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

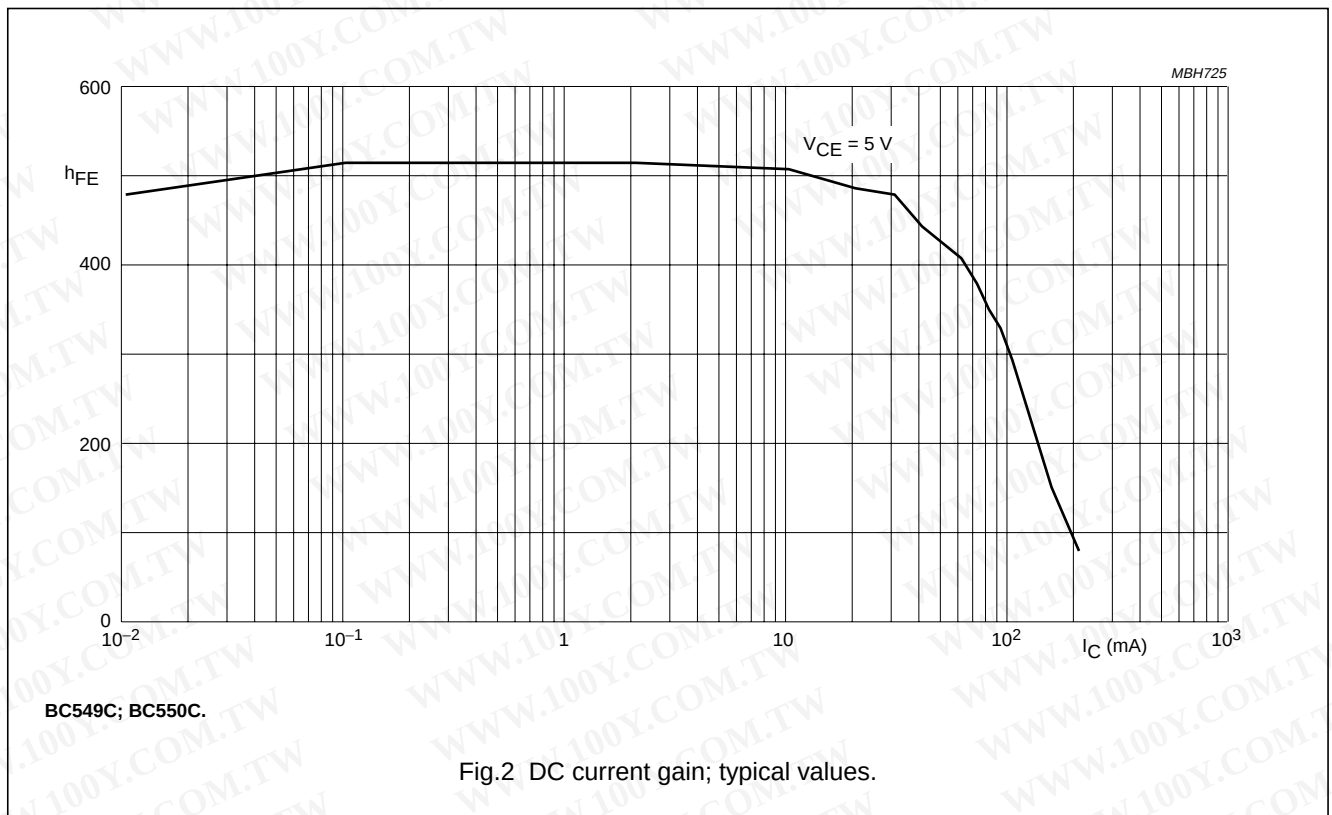
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	—	—	15	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ }^{\circ}\text{C}$	—	—	5	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	—	—	100	nA
h_{FE}	DC current gain BC549C; BC550C	$I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; \text{ see Fig.2}$	—	270	—	
		$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}; \text{ see Fig.2}$	420	520	800	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	—	90	250	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}$	—	200	600	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}; \text{ note 1}$	—	700	—	mV
		$I_C = 100\text{ mA}; I_B = 5\text{ mA}; \text{ note 1}$	—	900	—	mV
V_{BE}	base-emitter voltage	$I_C = 2\text{ mA}; V_{CE} = 5\text{ V}; \text{ note 2}$	580	660	700	mV
		$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; \text{ note 2}$	—	—	770	mV
C_c	collector capacitance	$I_E = I_C = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	—	1.5	—	pF
C_e	emitter capacitance	$I_C = I_E = 0; V_{EB} = 0.5\text{ V}; f = 1\text{ MHz}$	—	11	—	pF
f_T	transition frequency	$I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	100	—	—	MHz
F	noise figure	$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega; f = 10\text{ Hz to }15.7\text{ kHz}$	—	—	4	dB
		$I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega; f = 1\text{ kHz}; B = 200\text{ Hz}$	—	—	4	dB

Notes

1. V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.
2. V_{BE} decreases by about 2 mV/K with increasing temperature.

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PACKAGE OUTLINE

Plastic single-ended leaded (through hole) package; 3 leads

SOT54

